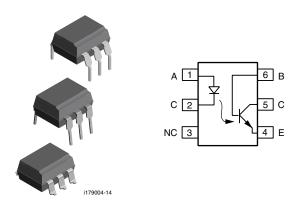


Optocoupler, Phototransistor Output, with Base Connection



DESCRIPTION

The CNY17 is an optically coupled pair consisting of a gallium arsenide infrared emitting diode optically coupled to a silicon NPN phototransitor.

Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output.

The CNY17 can be used to replace relays and transformers in many digital interface applications, as well as analog applications such as CRT modulation.

FEATURES

- Isolation test voltage: 5000 V_{RMS}
- Long term stability
- · Industry standard dual-in-line package
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC







AGENCY APPROVALS

- Underwriters lab file no. E52744
- cUL tested to CSA 22.2 bulletin 5A
- DIN EN 60747-5-2 (VDE 0884)
- BSI IEC 60950, IEC 60065
- FIMKO
- CQC (pending)

ORDERING INFORMATION									
C N Y 1 7 PART NUMBER	- # X	PACKAGE OPTION	# TAPE AND Option REEL Option > 8 to 1 and	10.16 mm Option 9					
AGENCY CERTIFIED/PACKAGE		CTR	(%)						
UL, cUL, BSI, FIMKO	40 to 80	63 to 125	100 to 200	160 to 320					
DIP-6	CNY17-1	CNY17-2	CNY17-3	CNY17-4					
DIP-6, 400 mil, option 6	CNY17-1X006	CNY17-2X006	CNY17-3X006	CNY17-4X006					
SMD-6, option 7	CNY17-1X007T (1)	CNY17-2X007T (1)	CNY17-3X007T (1)	CNY17-4X007T (1)					
SMD-6, option 9	CNY17-1X009T (1)	CNY17-2X009T (1)	CNY17-3X009T (1)	CNY17-4X009T (1)					
VDE, UL, CUL, BSI, FIMKO	40 to 80	63 to 125	100 to 200	160 to 320					
DIP-6	CNY17-1X001	CNY17-2X001	CNY17-3X001	CNY17-4X001					
DIP-6, 400 mil, option 6	CNY17-1X016	CNY17-2X016	CNY17-3X016	CNY17-4X016					
SMD-64, option 7	CNY17-1X017	CNY17-2X017T (1)	CNY17-3X017T (1)	CNY17-4X017T (1)					
SMD-6, option 9		CNY17-2X019T (1)							

Note

(1) Also available in tubes, do not put T on the end.



PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT			<u> </u>	
Reverse voltage		V_{R}	6	V
Forward current		I _F	60	mA
Forward surge current	t _p ≤ 10 μs	I _{FSM}	2.5	Α
LED power dissipation	at 25 °C	P _{diss}	70	mW
OUTPUT	·			
Collector emitter breakdown voltage		BV _{CEO}	70	V
Emitter base breakdown voltage		BV _{EBO}	7	V
Collector current		Ic	50	mA
Collector current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _C	100	mA
Power dissipation		P _{diss}	150	mW
COUPLER	·			
Isolation test voltage between emitter and detector	t = 1 s	V _{ISO}	5000	V_{RMS}
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Isolation thickness between emitter and detector			≥ 0.4	mm
Comparative tracking index per DIN IEC 112/VDE 0303, part 1			≥ 175	
Landa Cara and Calana and	V _{IO} = 500 V, T _{amb} = 25 °C	R _{IO}	≥ 10 ¹²	Ω
Isolation resistance	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	≥ 10 ¹¹	Ω
Storage temperature		T _{stg}	- 55 to + 150	°C
Operating temperature		T _{amb}	- 55 to + 100	°C
Soldering temperature (1)	2 mm from case, ≤ 10 s	T _{sld}	260	°C

Notes

(1) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT									
Forward voltage	I _F = 60 mA		V _F		1.39	1.65	V		
Breakdown voltage	I _R = 10 μA		V_{BR}	6			V		
Reverse current	V _R = 6 V		I _R		0.01	10	μA		
Capacitance	$V_R = 0 V, f = 1 MHz$		Co		25		pF		
Thermal resistance			R _{th}		750		K/W		
OUTPUT									
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz		C _{CE}		5.2		pF		
Collector base capacitance	$V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}$		C _{CB}		6.5		pF		
Emitter base capacitance	V _{CE} = 5 V, f = 1 MHz		C _{EB}		7.5		pF		
Thermal resistance			R _{th}		500		K/W		
COUPLER									
Collector emitter, saturation voltage	$V_F = 10 \text{ mA}, I_C = 2.5 \text{ mA}$		V _{CEsat}		0.25	0.4	V		
Coupling capacitance			C _C		0.6		pF		
	V _{CE} = 10 V	CNY17-1	I _{CEO}		2	50	nA		
Callector amitter leakage as		CNY17-2	I _{CEO}		2	50	nA		
Collector emitter, leakage current		CNY17-3	I _{CEO}		5	100	nA		
		CNY17-4	I _{CEO}		5	100	nA		

Note

• Minimum and maximum values were tested requierements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

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CURRENT TRANSFER RATIO (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT		
I _O /I _F		CNY17-1	CTR	40		80	%		
	$V_{CF} = 5 \text{ V}, I_{F} = 10 \text{ mA}$	CNY17-2	CTR	63		125	%		
	V _{CE} = 5 V, I _F = 10 IIIA	CNY17-3	CTR	100		200	%		
		CNY17-4	CTR	160		320	%		
		CNY17-1	CTR	13	30		%		
	$V_{CF} = 5 \text{ V}, I_{F} = 1 \text{ mA}$	CNY17-2	CTR	22	45		%		
	VCE = 3 V, IF = 1 IIIA	CNY17-3	CTR	34	70		%		
		CNY17-4	CTR	56	90		%		

SWITCHING CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
LINEAR OPERATION	without saturation)							
Turn-on time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		t _{on}		3		μs	
Rise time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		t _r		2		μs	
Turn-off time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		t _{off}		2.3		μs	
Fall time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		t _f		2		μs	
Cut-off frequency	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		f _{CO}		110		kHz	
SWITCHING OPERATI	ON (with saturation)							
	I _F = 20 mA	CNY17-1	t _{on}		3		μs	
Turn on time	I _F = 10 mA	CNY17-2	t _{on}		4.2		μs	
Turn-on time		CNY17-3	t _{on}		4.2		μs	
	I _F = 5 mA	CNY17-4	t _{on}		6		μs	
	I _F = 20 mA	CNY17-1	t _r		2		μs	
Dies time	I _F = 10 mA	CNY17-2	t _r		3		μs	
Rise time		CNY17-3	t _r		3		μs	
	I _F = 5 mA	CNY17-4	t _r		4.6		μs	
Turn-off time	I _F = 20 mA	CNY17-1	t _{off}		18		μs	
	I _F = 10 mA	CNY17-2	t _{off}		23		μs	
		CNY17-3	t _{off}		23		μs	
	I _F = 5 mA	CNY17-4	t _{off}		25		μs	
	I _F = 20 mA	CNY17-1	t _f		11		μs	
Fall time	I _F = 10 mA	CNY17-2	t _f		14		μs	
rali liille		CNY17-3	t _f		14		μs	
	I _F = 5 mA	CNY17-4	t _f		15		μs	

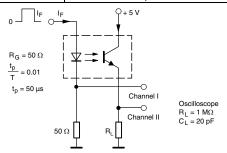


Fig. 1 - Test Circuit, Non-Saturated Operation

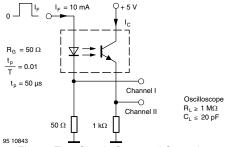


Fig. 2 - Test Circuit, Saturated Operation

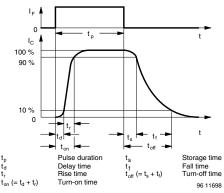


Fig. 3 - Switching Times

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

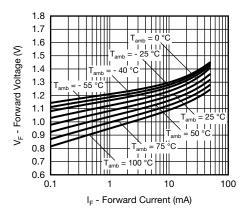


Fig. 4 - Forward Voltage vs. Forward Current

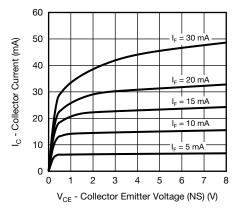


Fig. 5 - Collector Current vs. Collector Emitter Voltage (NS)

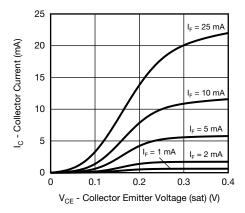


Fig. 6 - Collector Current vs. Collector Emitter Voltage (sat)

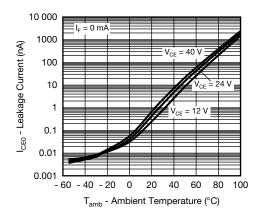


Fig. 7 - Leakage Current vs. Ambient Temperature

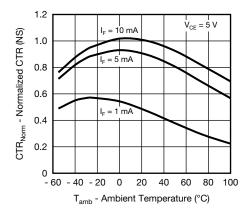


Fig. 8 - Normalized CTR (NS) vs. Ambient Temperature

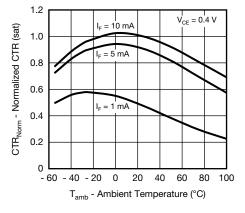


Fig. 9 - Normalized CTR (sat) vs. Ambient Temperature





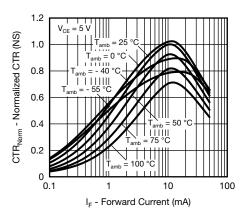


Fig. 10 - Normalized CTR (NS) vs. Forward Current

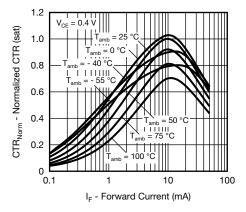


Fig. 11 - Normalized CTR (sat) vs. Forward Current

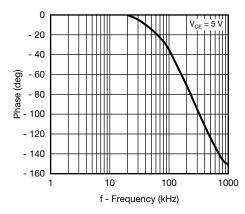


Fig. 12 - CTR Frequency vs. Phase Angle

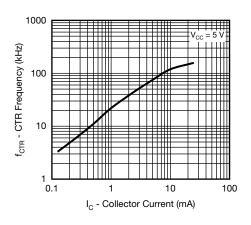


Fig. 13 - CTR Frequency vs. Collector Current

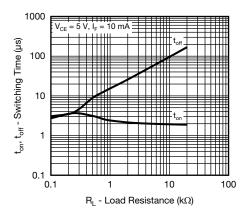
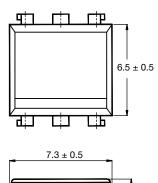
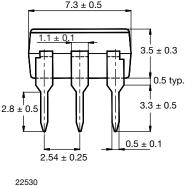
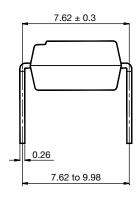


Fig. 14 - Switching Time vs. Load Resistance

PACKAGE DIMENSIONS in millimeters



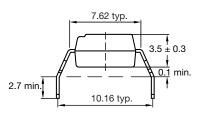


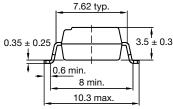


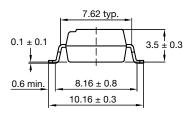
Option 6

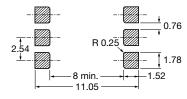
Option 7

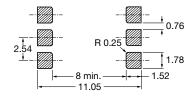
Option 9











20802-34 PACKAGE MARKING



Notes

- · VDE logo is only marked on option 1 parts. Option information is not marked on the part.
- Tape and reel suffix (T) is not part of the package marking.



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